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Electronic Supplementary Information

Memory characteristics of organic field-effect memory transistors modulated by nano-p-n junctions

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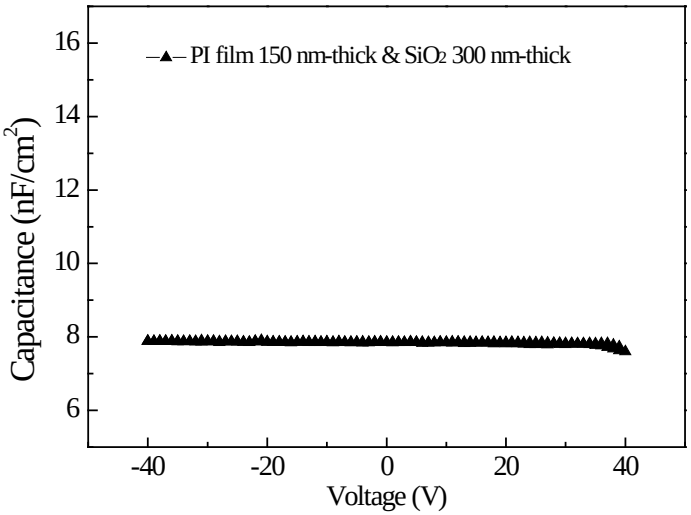

Fig. S1 The capacitances of PI/SiO_2/Si gate dielectrics measured at frequencies of 1 kHz.

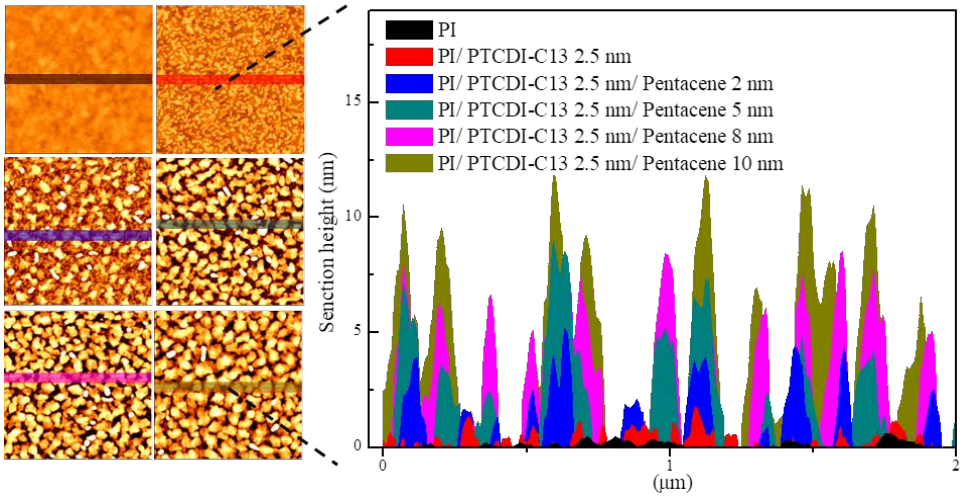

Fig. S2 The AFM images (left column) and related cross-section analyses (right column) of the pentacene films deposited onto PI/submonolayer PTCDI-C13.